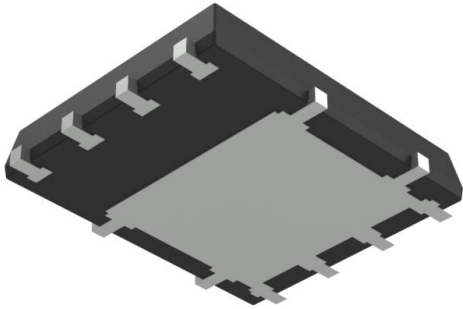


# DMTH10H025LPS-13 Datasheet

[www.digi-electronics.com](http://www.digi-electronics.com)



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	DMTH10H025LPS-13-DG
Manufacturer	<a href="#">Diodes Incorporated</a>
Manufacturer Product Number	DMTH10H025LPS-13
Description	MOSFET BVDSS: 61V-100V POWERDI50
Detailed Description	N-Channel 100 V 9.3A (Ta), 45A (Tc) 3.2W (Ta), 79W (Tc) Surface Mount PowerDI5060-8



Tel: +00 852-30501935

RFQ Email: [Info@DiGi-Electronics.com](mailto:Info@DiGi-Electronics.com)

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## Purchase and inquiry

Manufacturer Product Number:

DMTH10H025LPS-13

Series:

-

FET Type:

N-Channel

Drain to Source Voltage (Vdss):

100 V

Drive Voltage (Max Rds On, Min Rds On):

6V, 10V

Vgs(th) (Max) @ Id:

3V @ 250µA

Vgs (Max):

±20V

FET Feature:

-

Operating Temperature:

-55°C ~ 175°C (Tj)

Supplier Device Package:

PowerDI5060-8

Base Product Number:

DMTH10

Manufacturer:

Diodes Incorporated

Product Status:

Active

Technology:

MOSFET (Metal Oxide)

Current - Continuous Drain (Id) @ 25°C:

9.3A (Ta), 45A (Tc)

Rds On (Max) @ Id, Vgs:

23mOhm @ 20A, 10V

Gate Charge (Qg) (Max) @ Vgs:

21 nC @ 10 V

Input Capacitance (Ciss) (Max) @ Vds:

1477 pF @ 50 V

Power Dissipation (Max):

3.2W (Ta), 79W (Tc)

Mounting Type:

Surface Mount

Package / Case:

8-PowerTDFN

## Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0095

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99



DMTH10H025LPS

**100V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET**  
**PowerDI5060-8**

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> T <sub>c</sub> = +25°C
100V	23mΩ @ V <sub>GS</sub> = 10V	45A
	30mΩ @ V <sub>GS</sub> = 6V	38A

## Description

This new generation N-Channel Enhancement Mode MOSFET is designed to minimize R<sub>DS(ON)</sub> yet maintain superior switching performance. This device is ideal for use in notebook battery power management and load switch.

## Applications

- Synchronous rectifiers
- DC-DC converters
- Primary side switching

## Features

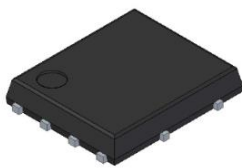
- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching – Ensures More Reliable And Robust End Application
- Low R<sub>DS(ON)</sub> – Minimizes On-State Losses
- Fast Switching Speed
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.**  
<https://www.diodes.com/quality/product-definitions/>
- **An automotive-compliant part is available under separate datasheet ([DMTH10H025LPSQ](#))**

## Mechanical Data

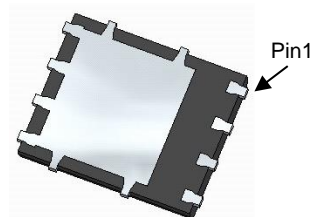
- Package: PowerDI<sup>®</sup>5060-8
- Package Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminal Finish - Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.097 grams (Approximate)

Site 1:

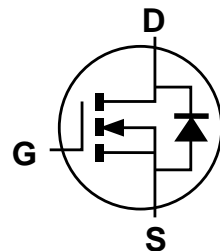
PowerDI5060-8



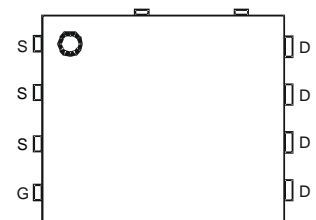
Top View



Bottom View

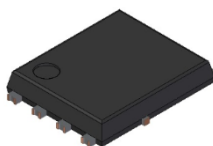


Internal Schematic

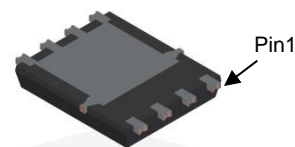
Top View  
Pin Configuration

Site 2:

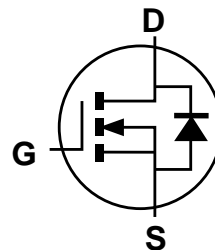
PowerDI5060-8 (SWP) (Type UX)



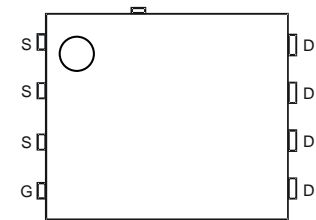
Top View



Bottom View



Internal Schematic

Top View  
Pin Configuration

Notes:

1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



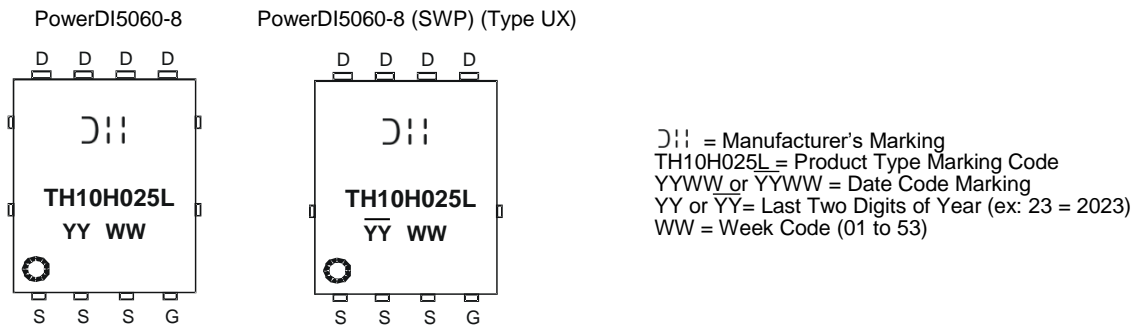
DMTH10H025LPS

## Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMTH10H025LPS-13	PowerDI5060-8	2500	Tape & Reel
DMTH10H025LPS-13	PowerDI5060-8 (SWP) (Type UX)	2500	Tape & Reel

Note: 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



## Maximum Ratings (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	100	V
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Continuous Drain Current, $V_{GS} = 10\text{V}$ (Note 5)	$I_D$	$T_A = +25^\circ\text{C}$	9.3
		$T_A = +100^\circ\text{C}$	6.6
Continuous Drain Current, $V_{GS} = 10\text{V}$ (Note 6)	$I_D$	$T_C = +25^\circ\text{C}$	45
		$T_C = +100^\circ\text{C}$	32
Pulsed Drain Current (10 $\mu\text{s}$ Pulse, Duty Cycle = 1%)	$I_{DM}$	90	A
Maximum Continuous Body Diode Forward Current (Note 6)	$I_S$	45	A
Pulsed Body Diode Forward Current (10 $\mu\text{s}$ Pulse, Duty Cycle = 1%)	$I_{SM}$	90	A
Avalanche Current (Note 7), $L=0.1\text{mH}$	$I_{AS}$	15.8	A
Avalanche Energy (Note 7), $L=0.1\text{mH}$	$E_{AS}$	12.5	mJ
Avalanche Current (Note 7), $L=3\text{mH}$	$I_{AS}$	8	A
Avalanche Energy (Note 7), $L=3\text{mH}$	$E_{AS}$	96	mJ

## Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	$P_D$	$T_A = +25^\circ\text{C}$	3.2
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	46
Total Power Dissipation (Note 6)	$P_D$	$T_C = +25^\circ\text{C}$	79
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	1.9
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +175	$^\circ\text{C}$

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.  
 6. Thermal resistance from junction to soldering point (on the exposed drain pad).  
 7. Short duration pulse test used to minimize self-heating effect.



DMTH10H025LPS

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b> (Note 7)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1mA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 80V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS</b> (Note 7)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	—	3	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	18	23	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A
		—	21	30		V <sub>GS</sub> = 6V, I <sub>D</sub> = 12.5A
Diode Forward Voltage	V <sub>SD</sub>	—	0.9	1.3	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 20A
<b>DYNAMIC CHARACTERISTICS</b> (Note 8)						
Input Capacitance	C <sub>iss</sub>	—	1477	—	pF	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V f = 1MHz
Output Capacitance	C <sub>oss</sub>	—	263	—		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	20	—		
Gate Resistance	R <sub>g</sub>	—	1.3	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge	Q <sub>g</sub>	—	21	—	nC	V <sub>DD</sub> = 50V, I <sub>D</sub> = 20A, V <sub>GS</sub> = 10V
Gate-Source Charge	Q <sub>gs</sub>	—	5.7	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	3.8	—		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	6.3	—	ns	V <sub>DD</sub> = 50V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A, R <sub>g</sub> = 6Ω
Turn-On Rise Time	t <sub>r</sub>	—	9.4	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	16.7	—		
Turn-Off Fall Time	t <sub>f</sub>	—	8.2	—		
Reverse Recovery Time	t <sub>RR</sub>	—	38.7	—	ns	I <sub>F</sub> = 20A, di/dt = 100A/μs
Reverse Recovery Charge	Q <sub>RR</sub>	—	53.7	—	nC	

Notes: 7. Short duration pulse test used to minimize self-heating effect.  
8. Guaranteed by design. Not subject to product testing.



**DMTH10H025LPS**

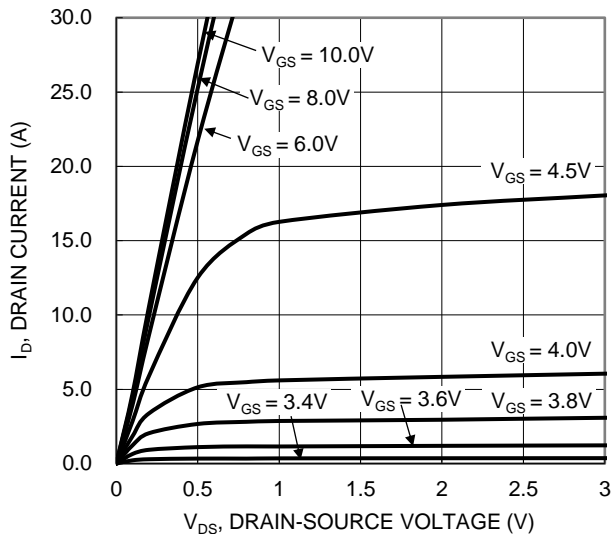


Figure 1. Typical Output Characteristic

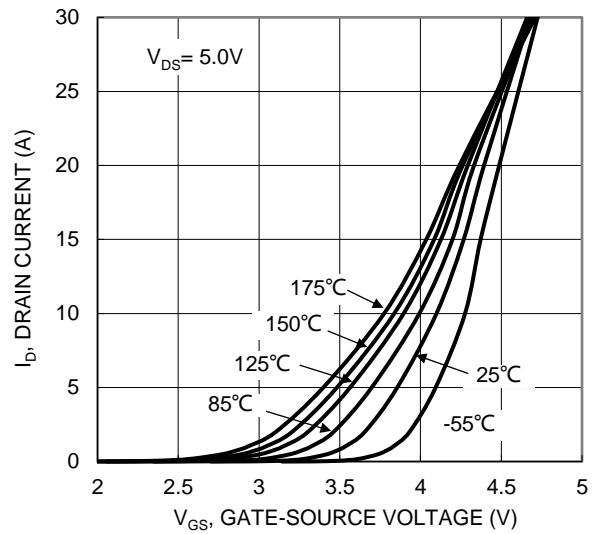


Figure 2. Typical Transfer Characteristic

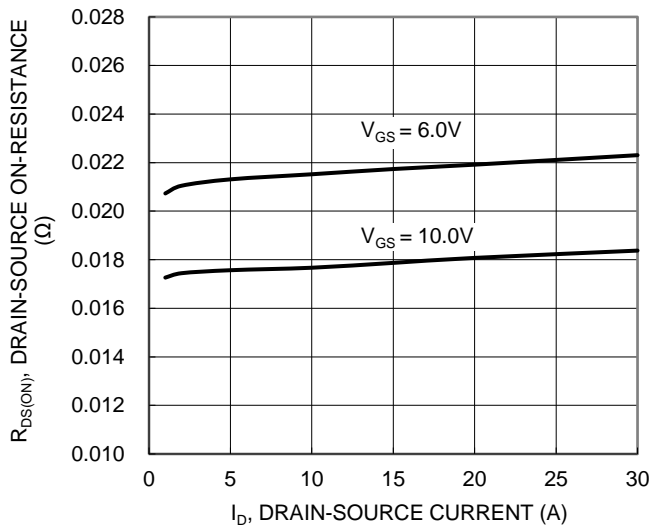


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

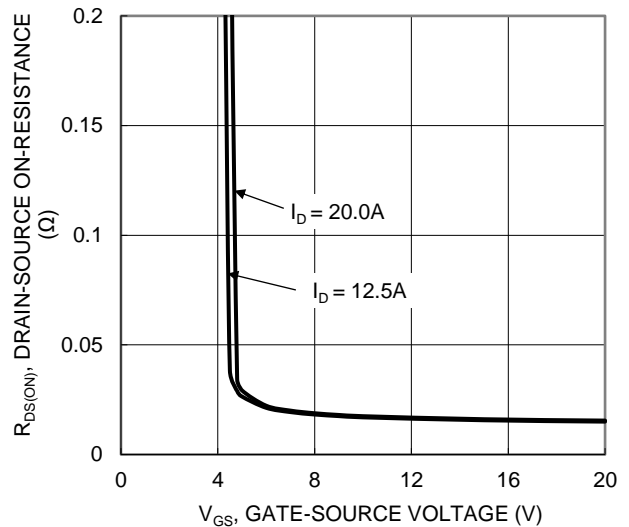


Figure 4. Typical Transfer Characteristic

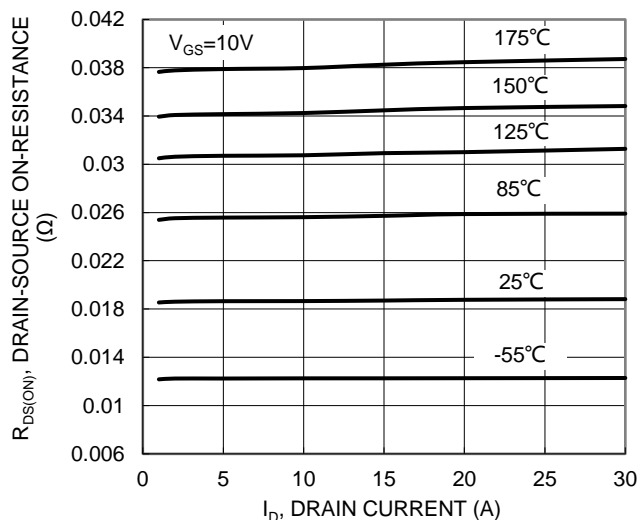


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

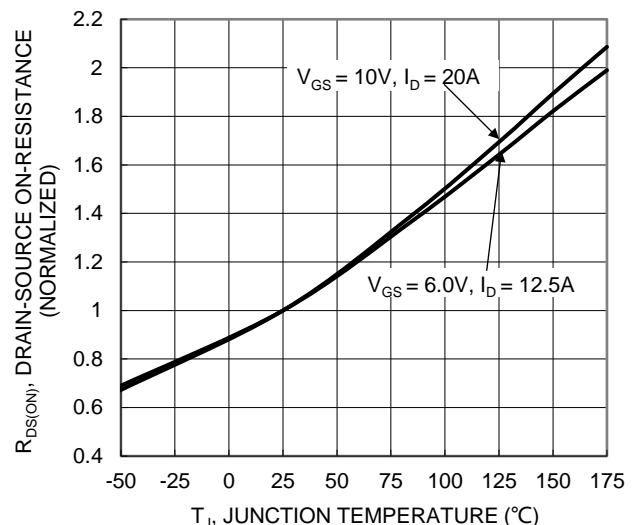


Figure 6. On-Resistance Variation with Temperature



**DMTH10H025LPS**

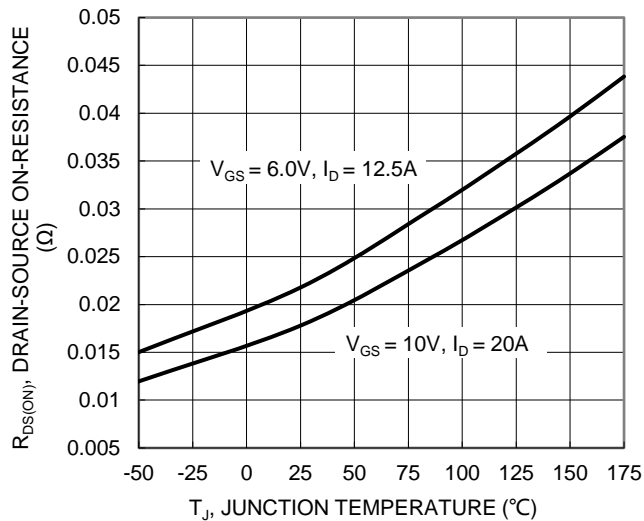


Figure 7. On-Resistance Variation with Temperature

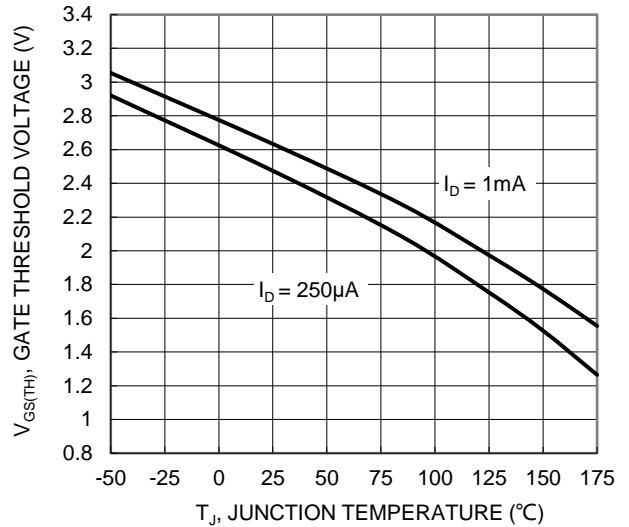


Figure 8. Gate Threshold Variation vs. Junction Temperature

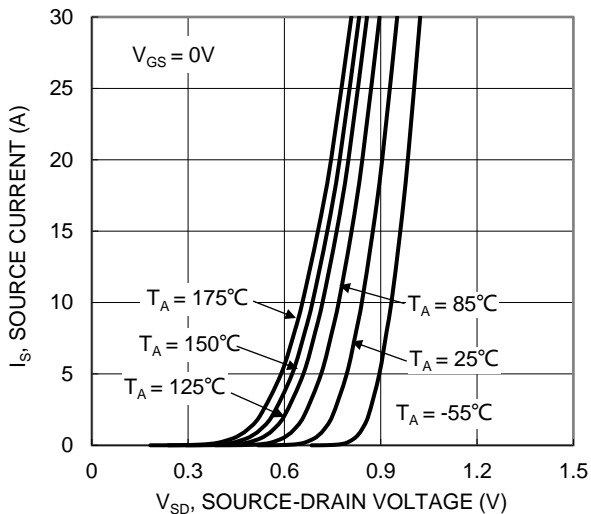


Figure 9. Diode Forward Voltage vs. Current

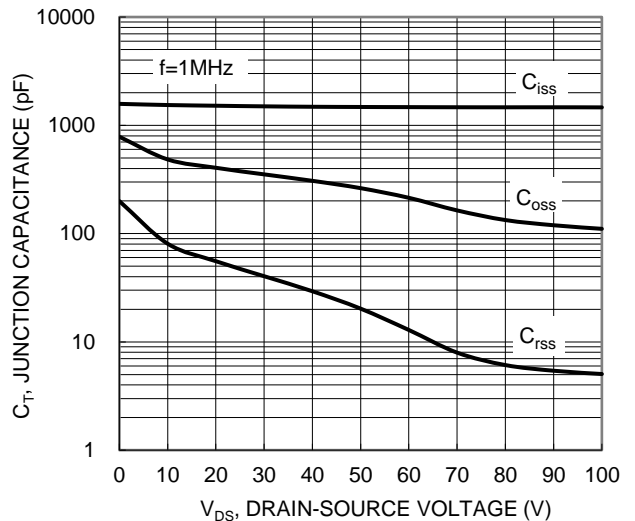


Figure 10. Typical Junction Capacitance

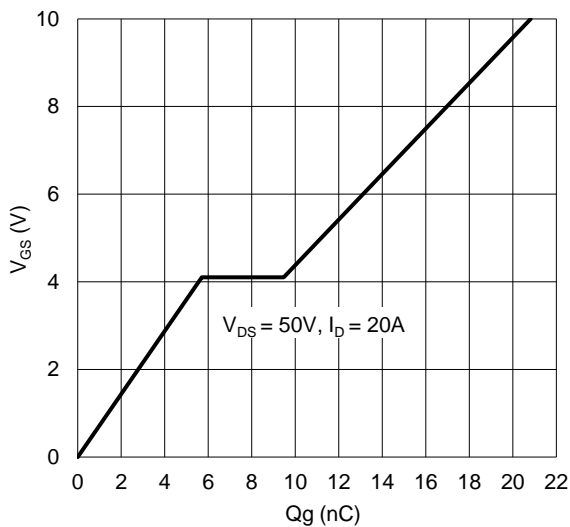


Figure 11. Gate Charge

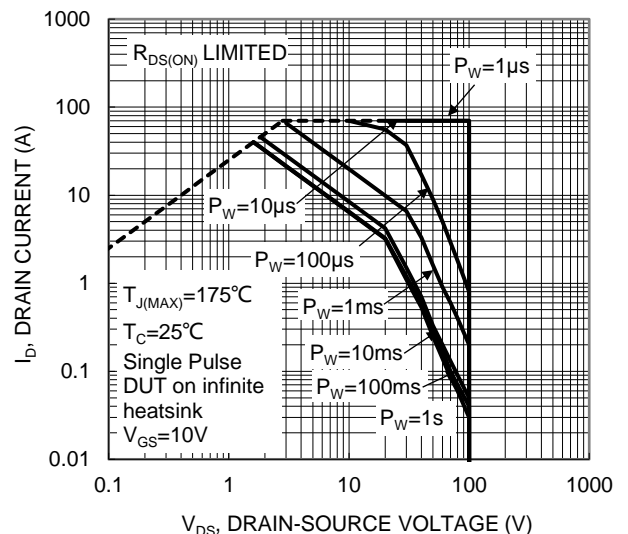


Figure 12. SOA, Safe Operation Area



DMTH10H025LPS

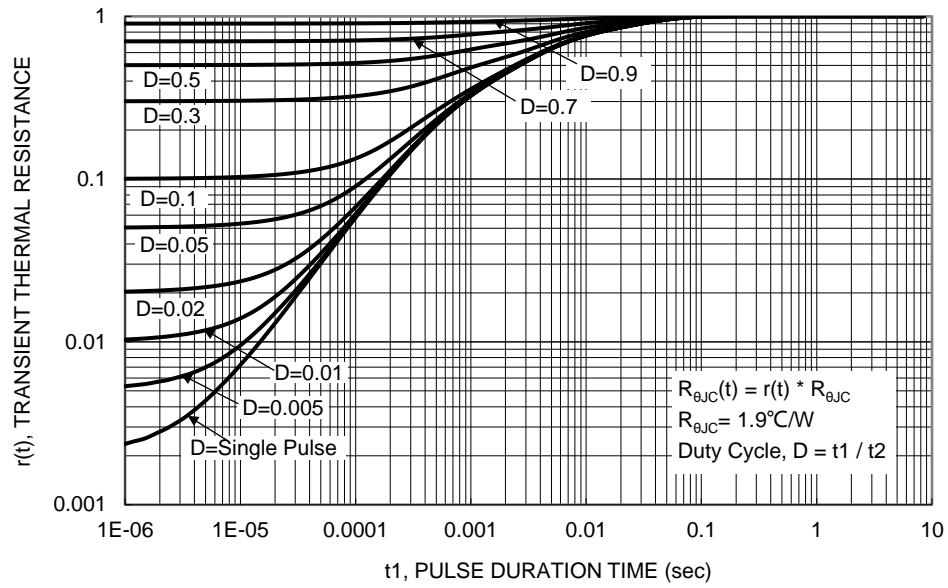


Figure 13. Transient Thermal Resistance

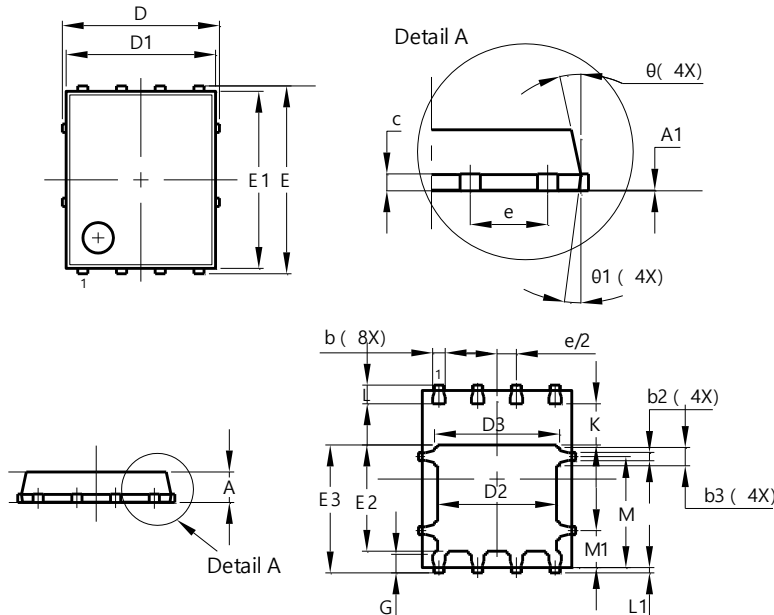


## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### Site 1:

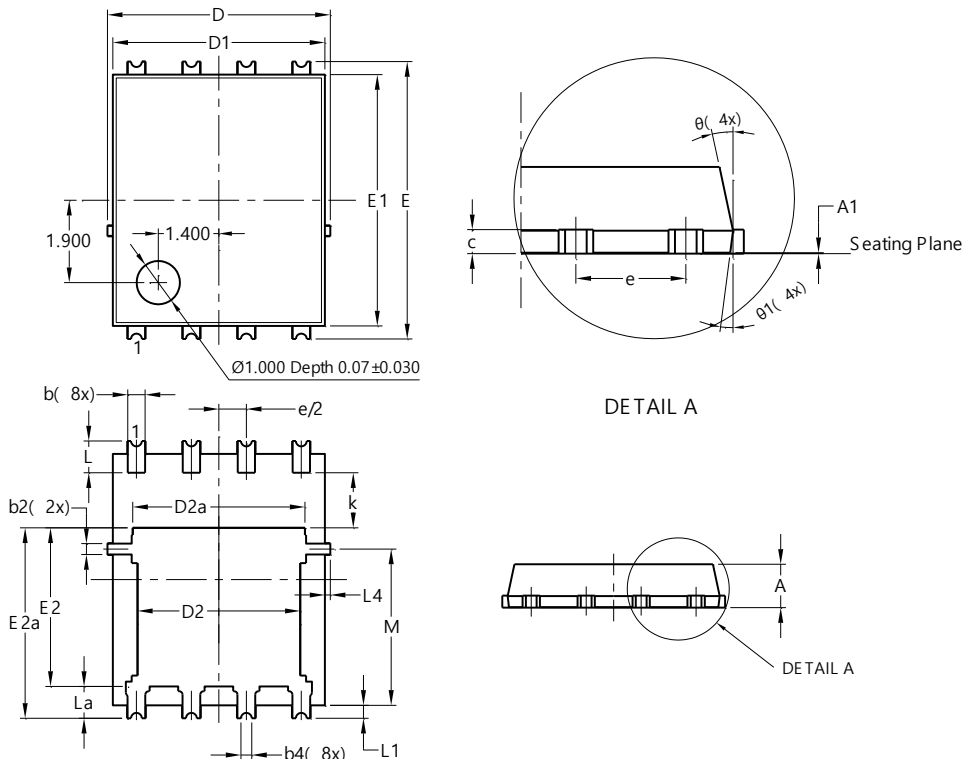
#### PowerDI5060-8



PowerDI5060-8			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0.00	0.05	—
b	0.33	0.51	0.41
b2	0.200	0.350	0.273
b3	0.40	0.80	0.60
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.70	4.10	3.90
D3	3.90	4.30	4.10
E	6.15 BSC		
E1	5.60	6.00	5.80
E2	3.28	3.68	3.48
E3	3.99	4.39	4.19
e	1.27 BSC		
G	0.51	0.71	0.61
K	0.51	—	—
L	0.51	0.71	0.61
L1	0.100	0.200	0.175
M	3.235	4.035	3.635
M1	1.00	1.40	1.21
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

### Site 2:

#### PowerDI5060-8/SWP (Type UX)



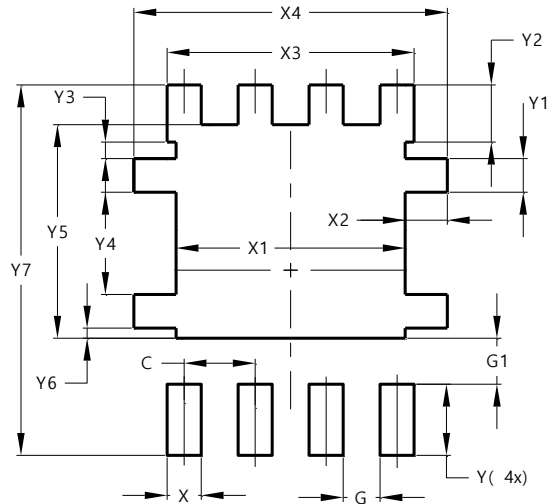
PowerDI5060-8/SWP (Type UX)			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0	0.05	--
b	0.30	0.50	0.41
b2	0.20	0.35	0.25
b4	0.25REF		
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.56	3.96	3.76
D2a	3.78	4.18	3.98
E	6.40 BSC		
E1	5.60	6.00	5.80
E2	3.46	3.86	3.66
E2a	4.195	4.595	4.395
e	1.27BSC		
k	1.05	--	--
L	0.635	0.835	0.735
La	0.635	0.835	0.735
L1	0.200	0.400	0.300
L1a	0.050REF		
L4	0.025	0.225	0.125
M	3.205	4.005	3.605
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### Site 1:

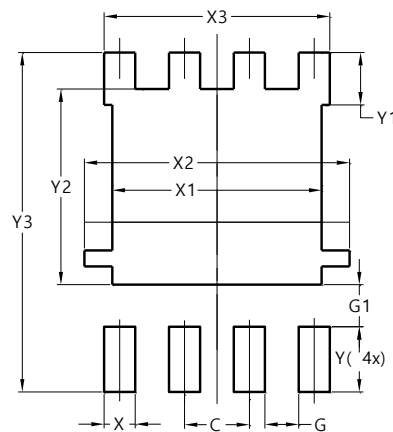
#### PowerDI5060-8



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

### Site 2:

#### PowerDI5060-8/SWP (Type UX)



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	5.190
X3	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610

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